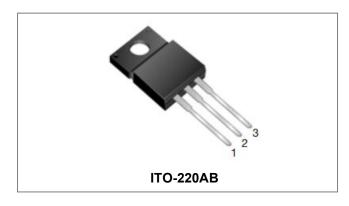




MBRF10150CT (CTR) SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

Circuit Diagram





Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

| Characteristics | Symbol | Condition | Max. | Units |
|--|--|---|------------------------------|-------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | - | 150 | V |
| Average Rectified Forward Current | I _{F (AV)} | 50% duty cycle @Tc=100°C, rectangular wave form | 5(Per Leg) 10(Per Device) | Α |
| Peak One Cycle Non-Repetitive Surge Current(Per Leg) | I _{FSM} | 8.3ms, Half Sine pulse | 138 | А |

Electrical Characteristics:

| Characteristics | Symbol | Condition | Тур. | Max. | Units |
|--|------------------|---|-------|--------|-------|
| Forward Voltage Drop(Per Leg)* | V _{F1} | @5A, Pulse, T _J = 25 °C | 0.82 | 0.93 | V |
| | V _{F2} | @5A, Pulse, T _J = 125 °C | 0.68 | 0.73 | V |
| Reverse Current(Per Leg)* | I _{R1} | @V _R = rated V _R , T _J = 25 °C | 0.002 | 1.0 | mA |
| | I _{R2} | @V _R = rated V _R , T _J = 125 °C | 1.5 | 7.0 | mA |
| Junction Capacitance(Per Leg) | Ст | @V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz | 110 | 200 | pF |
| Series Inductance(Per Leg) | Ls | Measured lead to lead 5 mm from package body | 8.0 | - | nH |
| Voltage Rate of Change | dv/dt | - | - | 10,000 | V/μs |
| RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T _A = 25 °C) | V _{ISO} | Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction. | - | 4500 | V |
| , | | Clip mounting, the epoxy body is inside the heatsink. | - | 3500 | |
| | | Screw mounting, the epoxy body is inside the heatsink. | - | 1500 | |

^{*} Pulse width < 300 µs, duty cycle < 2%

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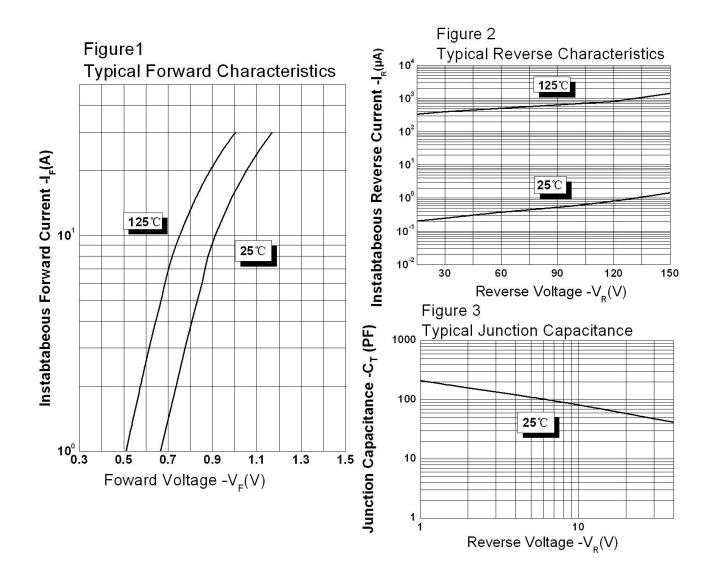




Thermal-Mechanical Specifications:

| Characteristics | Symbol | Condition | Specification | Units |
|---|------------------|--------------|---------------|-------|
| Junction Temperature | TJ | - | -55 to +150 | °C |
| Storage Temperature | T _{stg} | - | -55 to +150 | °C |
| Typical Thermal Resistance Junction to Case | $R_{	heta JC}$ | DC operation | 4.5 | °C/W |
| Approximate Weight | wt | - | 2 | g |
| Case Style | ITO-220AB | | | |

Ratings and Characteristics Curves



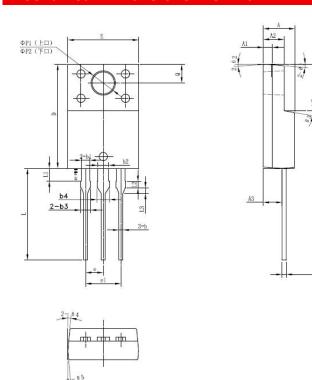
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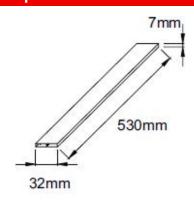


Mechanical Dimensions ITO-220AB

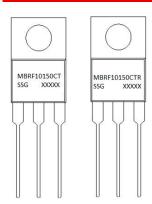


| OVMBOL | Millimeters | | | |
|------------------|-------------|-------|-------|--|
| SYMBOL | MIN. | TYP. | MAX. | |
| Α | 4.30 | 4.50 | 4.70 | |
| A1 | 1.10 | 1.30 | 1.50 | |
| A2 | 2.80 | 3.00 | 3.20 | |
| A3 | 2.50 | 2.70 | 2.90 | |
| b | 0.50 | 0.60 | 0.75 | |
| b1 | 1.10 | 1.20 | 1.35 | |
| b2 | 1.50 | 1.60 | 1.75 | |
| b3 | 1.20 | 1.30 | 1.45 | |
| b4 | 1.60 | 1.70 | 1.85 | |
| С | 0.50 | 0.60 | 0.75 | |
| D | 14.80 | 15.00 | 15.20 | |
| E | 9.96 | 10.16 | 10.36 | |
| е | | 2.55 | | |
| e1 | | 5.10 | | |
| H1 | 6.50 | 6.70 | 6.90 | |
| L | 12.70 | 13.20 | 13.70 | |
| L1 | 1.60 | 1.80 | 2.00 | |
| L2 | 0.80 | 1.00 | 1.20 | |
| L3 | 0.60 | 0.80 | 1.00 | |
| ΦP1 (上□) | 3.30 | 3.50 | 3.70 | |
| ΦP2 (下口) | 2.99 | 3.19 | 3.39 | |
| Q | 2.50 | 2.70 | 2.90 | |
| Θ1 | | 5° | | |
| Θ2 | | 4° | | |
| Θ3 | | 10° | | |
| Θ4 | | 5° | | |
| Θ5 | | 5° | | |

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 MBR
 = Device Type

 F
 = Package type

 10
 = Forward Current (10A)

 150
 = Reverse Voltage (150V)

 CT(CTR)
 = Configuration

 SSG
 = SSG

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

| Device | Package | Shipping | |
|------------------|--------------------|--------------|--|
| MBRF10150CT(CTR) | ITO-220AB(Pb-Free) | 50 pcs/ tube | |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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